



10N60K-MTQ

Power MOSFET

10A, 600V N-CHANNEL POWER MOSFET

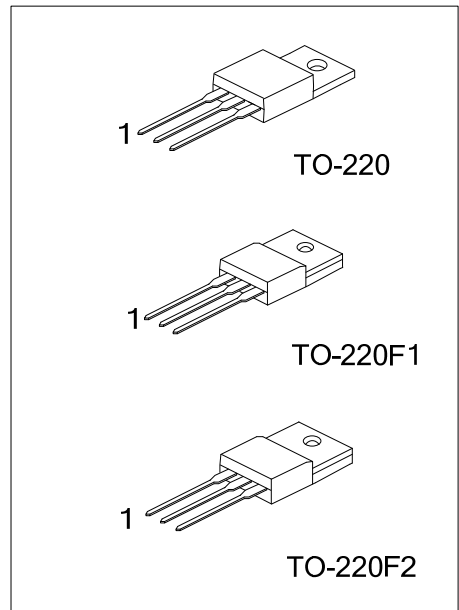
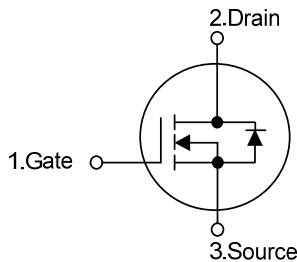
■ DESCRIPTION

The UTC **10N60K-MTQ** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

- * $R_{DS(ON)} < 1.0 \Omega @ V_{GS} = 10 V, I_D = 5.0 A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



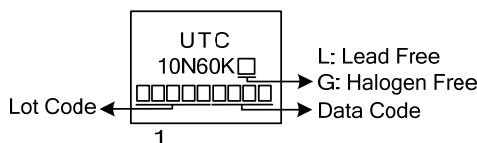
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N60KL-TF3-T	10N60KG-TF3-T	TO-220F	G	D	S	Tube
10N60KL-TF1-T	10N60KG-TF1-T	TO-220F1	G	D	S	Tube
10N60KL-TF2-T	10N60KG-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N60KG-TF3-T</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) T: Tube (2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	10	A
Pulsed Drain Current (Note 2)		I_{DM}	40	A
Avalanche Current (Note 2)		I_{AR}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	365	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	ns
Power Dissipation	TO-220	P_D	156	W
	TO-220F1		50	W
	TO-220F2		52	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 11.4\text{mH}$, $I_{AS} = 8.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 10\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

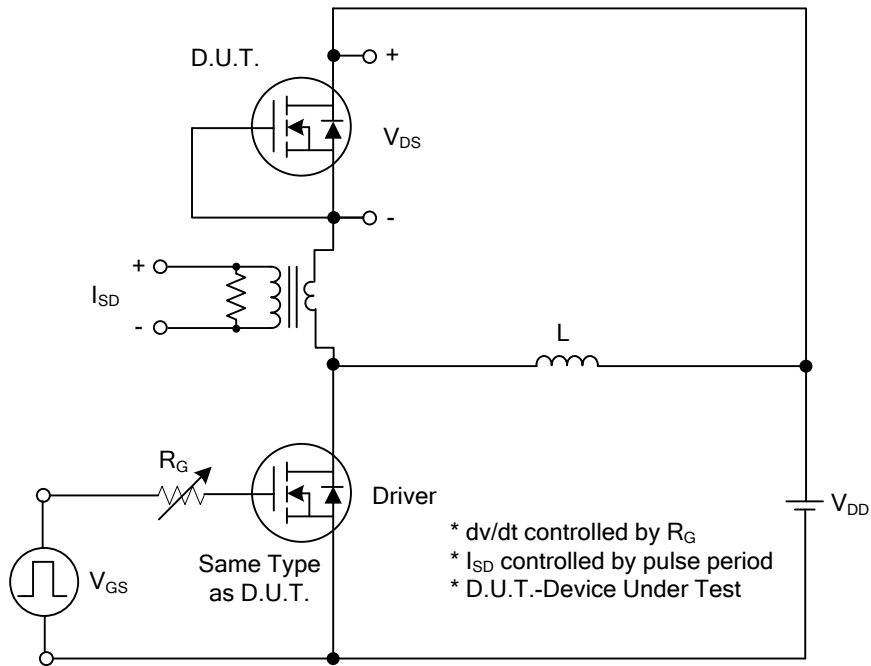
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.8	$^\circ\text{C}/\text{W}$
	TO-220F1		2.5	
	TO-220F2		2.4	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

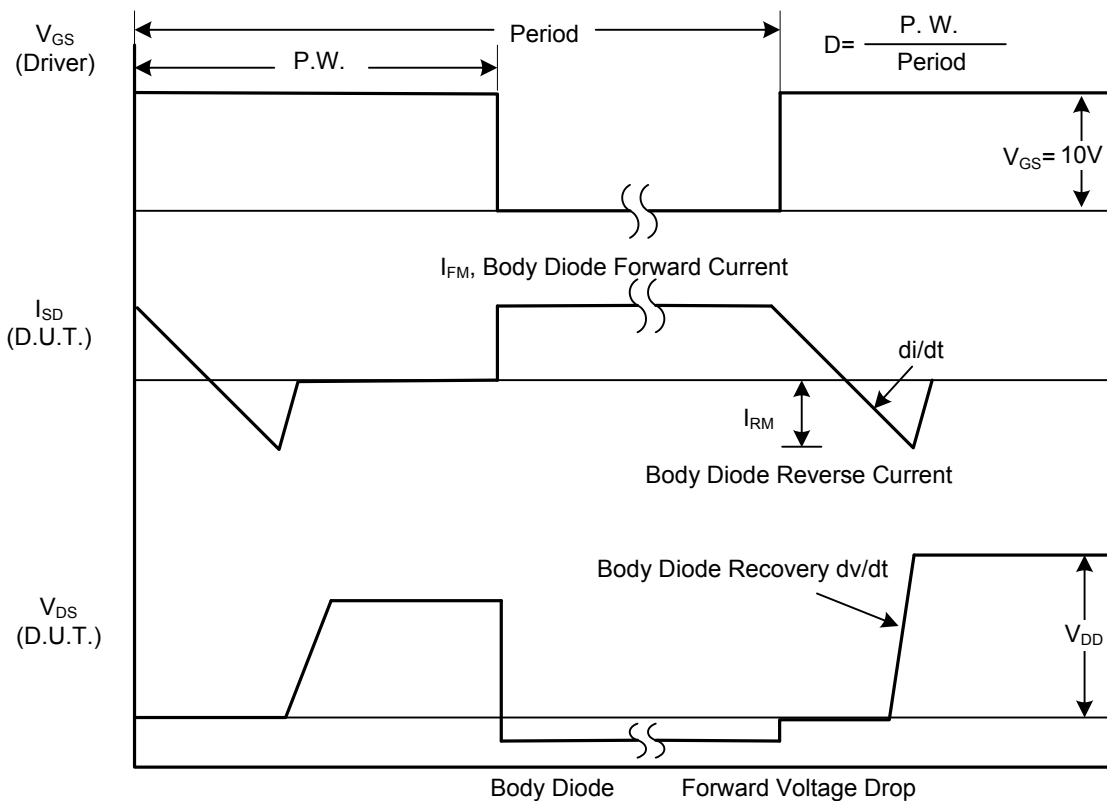
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5.0A			1.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		1120		pF
Output Capacitance	C _{OSS}			120		pF
Reverse Transfer Capacitance	C _{RSS}			13		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =50V, I _D =1.3A, I _G =100μA V _{GS} =10V (Note 1,2)		28		nC
Gate-Source Charge	Q _{GS}			8		nC
Gate-Drain Charge	Q _{GD}			6		nC
Turn-On Delay Time (Note 1)	t _{D(ON)}	V _{DD} =30V, I _D =0.5A, R _G =25Ω, V _{GS} =10V (Note 1,2)		80		ns
Turn-On Rise Time	t _R			89		ns
Turn-Off Delay Time	t _{D(OFF)}			125		ns
Turn-Off Fall Time	t _F			64		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				40	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	V _{GS} = 0 V, I _S = 10 A			1.4	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
 2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

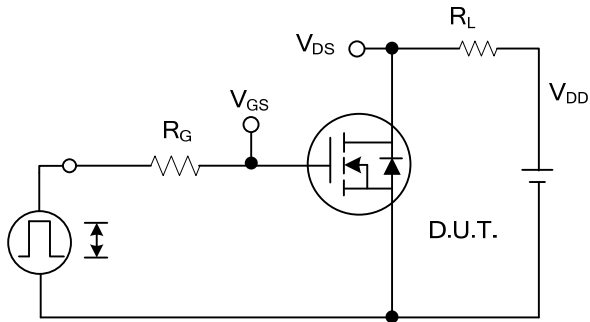


Peak Diode Recovery dv/dt Test Circuit

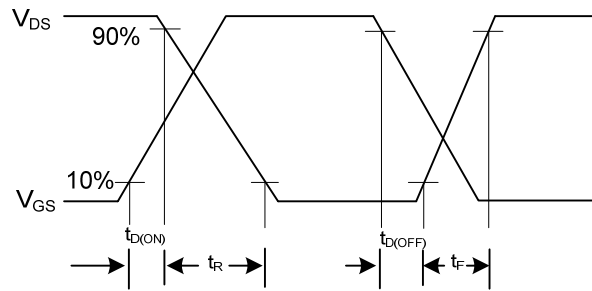


Peak Diode Recovery dv/dt Waveforms

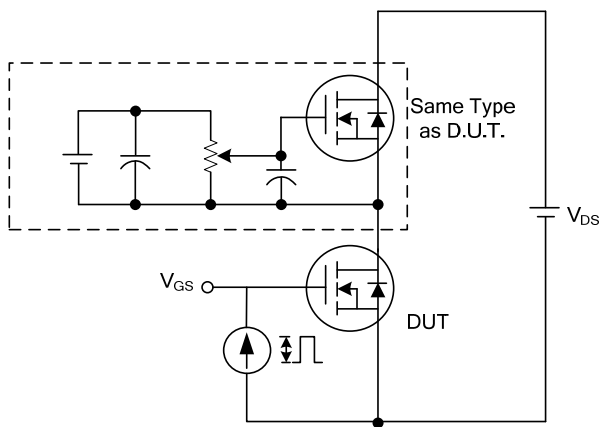
TEST CIRCUITS AND WAVEFORMS (Cont.)



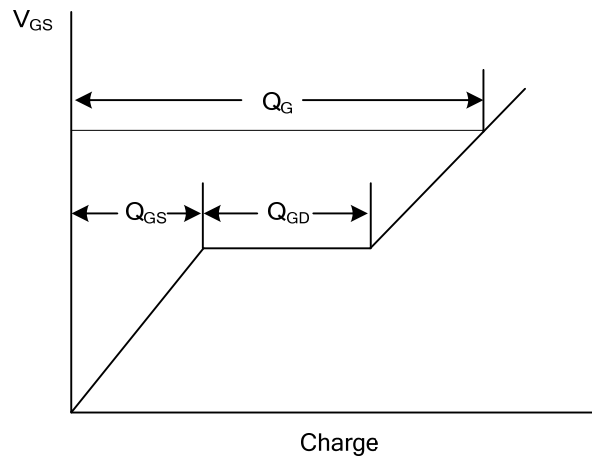
Switching Test Circuit



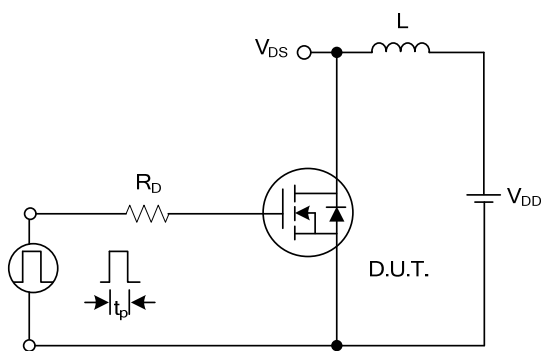
Switching Waveforms



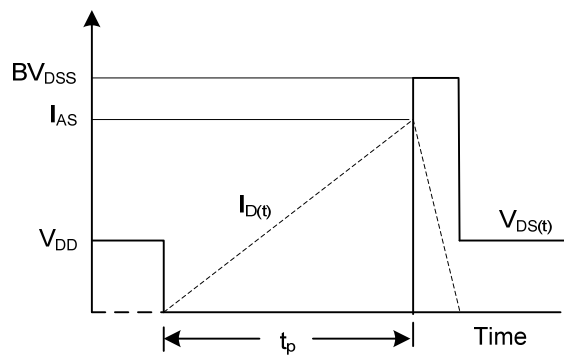
Gate Charge Test Circuit



Gate Charge Waveform

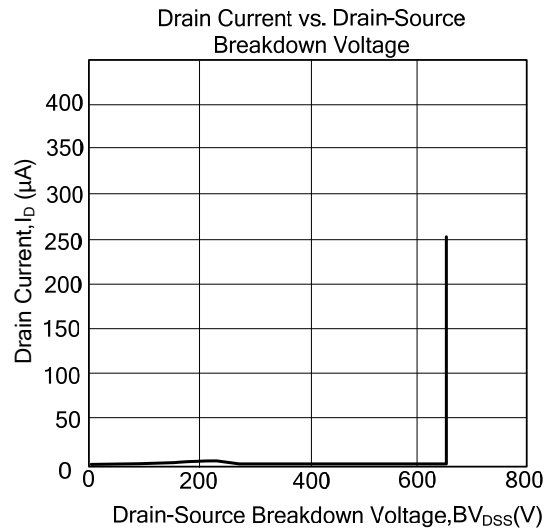
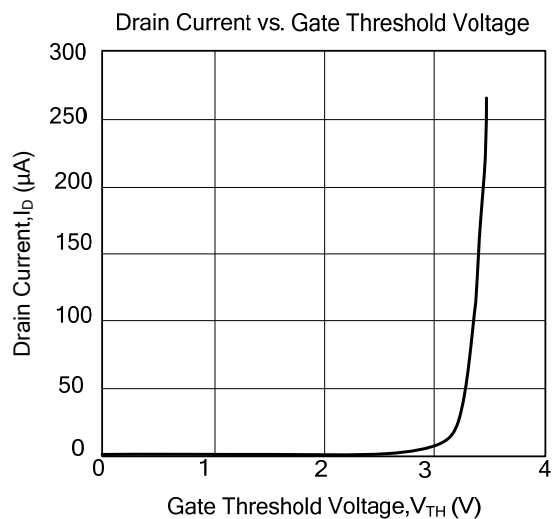
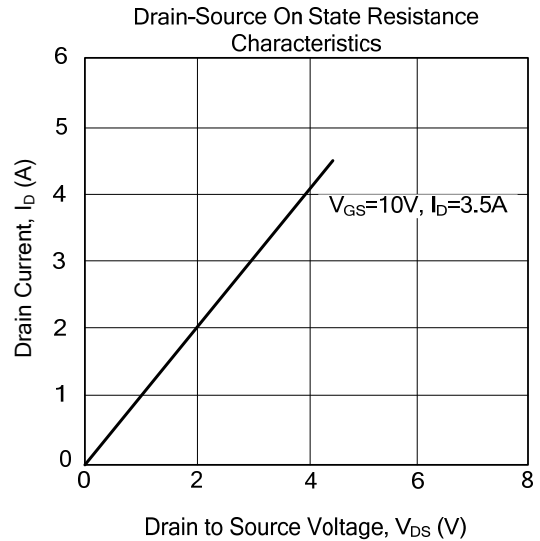
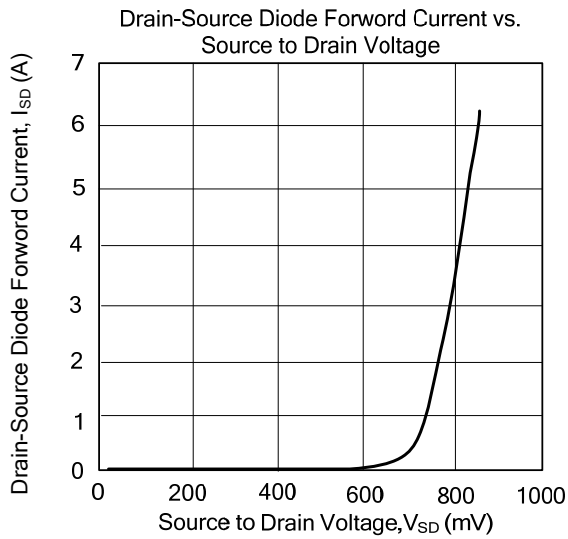


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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